

FORMING METHOD OF RESIST PATTERN AND FORMING METHOD OF ANTIREFLECTION FILM

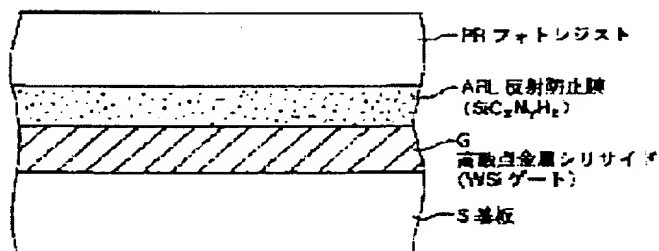
Patent number: JP8078322
Publication date: 1996-03-22
Inventor: OGAWA TORU; GOCHO TETSUO
Applicant: SONY CORP
Classification:
- international: H01L21/027; C30B25/14; G03F7/11; G03F7/26
- european:
Application number: JP19950169089 19950704
Priority number(s):

[View INPADOC patent family](#)

Abstract of JP8078322

PURPOSE: To provide a stable forming method of a resist pattern and a new forming method of an antireflection film excellently even at the time of the fine resist pattern.

CONSTITUTION: An antireflection film ARL composed of a silicon oxide film (SiO_xNy or SiO_xNyHz) containing at least nitrogen is formed onto a foundation substrate S directly or through another layer. A photo-resist PR is formed onto the antireflection film ARL directly or through another layer. The photo-resist PR is exposed, and a mask pattern is transferred. It is favorable that an antireflection film having a reflection refractive index (n) from 1.2 to 3.4 in an exposure wavelength of 150-450nm, an absorption refractive index (k) from 0.16 to 0.72 and film thickness from 10nm to 100nm is formed as the antireflection film.



Data supplied from the esp@cenet database - Worldwide

EV372455910